

Title (en)

PROCESS FOR MANUFACTURING ROUNDED POLYSILICON ELECTRODES ON SEMICONDUCTOR COMPONENTS

Title (de)

VERFAHREN ZUR HERSTELLUNG VON VERRUNDETEN POLYSILIZIUMELEKTRODEN AUF HALBLEITERBAUELEMENTEN

Title (fr)

PROCEDE DE PRODUCTION D'ELECTRODES EN POLYSILICIUM ARRONDIES SUR DES COMPOSANTS A SEMI-CONDUCTEURS

Publication

**EP 1728268 A1 20061206 (DE)**

Application

**EP 06700494 A 20060113**

Priority

- EP 2006000287 W 20060113
- DE 102005004596 A 20050201

Abstract (en)

[origin: WO2006081929A1] A polysilicon layer for a polysilicon electrode (8) is structured by means of a lacquer mask (5) and an auxiliary layer (4) made of a material suitable as antireflection layer. The auxiliary layer (4) is provided with lateral cavities such that the polysilicon electrode is etched with rounded edges (7). The auxiliary layer is preferably made of a soluble material and with a thickness ranging from 70 nm to 80 nm. A base layer (2) may be provided as gate dielectric of storage cell transistors and additionally as etching stop layer.

IPC 8 full level

**H01L 21/027** (2006.01); **H01L 21/28** (2006.01)

CPC (source: EP US)

**H01L 21/0276** (2013.01 - EP US); **H01L 21/32139** (2013.01 - EP US); **H01L 29/40114** (2019.07 - EP US)

Citation (search report)

See references of WO 2006081929A1

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DOCDB simple family (publication)

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DOCDB simple family (application)

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